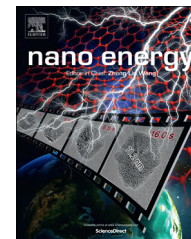


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Theoretical systems of triboelectric nanogenerators

Simiao Niu^a, Zhong Lin Wang^{a,b,*}

^a*School of Materials Science and Engineering, Georgia Institute of Technology, Atlanta, GA 30332-0245, USA*

^b*Beijing Institute of Nanoenergy and Nanosystems, Chinese Academy of Sciences, Beijing 100083, China*

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Abstract

Triboelectric nanogenerator (TENG) technology based on contact electrification and electrostatic induction is an emerging new mechanical energy harvesting technology with numerous advantages. The current area power density of TENGs has reached 313 W/m^2 and their volume energy density has reached 490 kW/m^3 . In this review, we systematically analyzed the theoretical system of triboelectric nanogenerators (TENGs). Starting from the physics of TENGs, we thoroughly discussed the fundamental working principle of TENGs and simulation method. Then the intrinsic output characteristics, load characteristics, and optimization strategy is in-depth discussed. TENGs have inherent capacitive behavior and their governing equation is their V-Q-x relationship. There are two capacitance formed between the tribocharged dielectric surface and the two metal electrodes, respectively. The ratio of these two capacitances changes with the position of this dielectric surface, inducing electrons to transfer between the metal electrodes under SC condition. This is the core working mechanism of triboelectric generators and different TENG fundamental modes can be classified based on the changing behavior of these two capacitances. Their first-order lumped-parameter equivalent circuit model is a voltage source in series with a capacitor. Their resistive load characteristics have a “three-working-region” behavior because of the impedance match mechanism. Besides, when TENGs are utilized to charge a capacitor with a bridge rectifier in multiple motion cycles, it is equivalent to utilizing a constant DC voltage source with an internal resistance to charge. The optimization techniques for all TENG fundamental modes are also discussed in detail. The theoretical system reviewed in this work provides a theoretical basis of TENGs and can be utilized as a guideline for TENG designers to continue improving TENG output performance.

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*Corresponding author at: School of Materials Science and Engineering, Georgia Institute of Technology, Atlanta, GA 30332-0245, USA.

E-mail address: zhong.wang@mse.gatech.edu (Z.L. Wang).

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1 Introduction

3 The tremendous development of portable electronics and
 4 sensor networks makes it an urgent requirement to develop
 5 sustainable and stable energy sources for them. Powering
 6 them entirely by batteries has become more and more
 7 unpractical and unfavorable, mainly for the limited battery
 8 lifetime, large scope of distribution of these kinds of
 9 electronic devices, and potential health and environmental
 10 hazards. Therefore, new technologies that can harvest
 11 energy from ambient environment as sustainable power
 12 sources are emerging research fields, called nano-energy
 13 research, which focuses on the applications of nanomaterials
 14 and nanotechnology for harvesting energy for powering
 15 micro/nanosystems. Recently, triboelectric nanogenerators
 16 (TENGs) based on contact electrification and electrostatic
 17 induction have become a promising technology in mechanical
 18 energy harvesting, which shows unique merits including
 19 large output power, high efficiency, low weight and cost
 20 effective materials, and simple fabrication [1]. Through
 21 3 years research, the area power density of TENGs has
 22 reached 313 W/m^2 and their volume energy density has
 23 reached 490 kW/m^3 [2]. The current developed highest
 24 mechanical energy conversion efficiency has reached about
 25 85% [3]. Triboelectric nanogenerators have been utilized as
 26 direct power source to charge a mobile phone battery [4]
 27 and worked as self-powered active sensors [5]. However,
 28 there are still requirements for continuing improving their
 29 output performance for more and more practical applica-
 30 tions, which demands rational design and careful optimiza-
 31 tion of both materials and structures especially when the
 32 current TENG performance is already very high. Moreover,
 33 similar to the development of CMOS integrated circuits and
 34 systems, the fully-integrated energy harvesting systems that
 35 contain TENGs, power management circuits, signal proces-
 36 sing circuits, energy storage elements, and/or load circuits
 37 are essential for the practical applications of the TENGs.
 38 Theoretical simulation plays a key role in understanding the
 39 working mechanism and analyzing the output performance
 40 of the entire system. Finally, from methodology point of
 41 view, simulation is always a necessary step in the whole
 42 device design process, because performing control experi-
 43 ments is usually time-consuming and not cost-effective.
 44 Thus a thorough theoretical understanding of TENGs is
 45 completely urgent in the whole research field. This knowl-
 46 edge can help choosing the appropriate TENG structure and
 47 materials, avoid designs which will greatly harm the output
 48 performance, and choose suitable system-level topologies
 49 for integrated energy harvesting systems.

50 The objective of this paper is to give a summary about
 51 the fundamental theory research of the triboelectric nano-
 52 generator (TENG). First, we will discuss the governing
 53 equation, equivalent circuit model, and simulation method.
 54 Then, the basic output characteristics (open-circuit voltage,
 55 short-circuit transferred charges, and inherent capacitance)
 56 of four fundamental TENG modes are discussed in detail.
 57 Moreover, resistive load and capacitive load characteristics
 58 are shown. Finally, based on the above basic information,
 59 we will discuss some advanced TENG structures and optimi-
 60 zation techniques for each fundamental TENG modes.

Basics of triboelectric nanogenerators

Inherent capacitive behavior and governing equations: V - Q - x relationship

61 The fundamental working principle of TENGs is a conjuga-
 62 tion of contact electrification and electrostatic induction.
 63 Contact electrification provides static polarized charges and
 64 electrostatic induction is the main mechanism that converts
 65 mechanical energy to electricity. Since the most fundamen-
 66 tal device based on electrostatics is a capacitor, fundamen-
 67 tally TENG will have inherent capacitive behavior [6].

68 An arbitrary TENG is analyzed to unveil its inherent
 69 capacitive behavior. For any triboelectric generators, there
 70 are pair of materials which are face to each other (called
 71 tribo-pairs). The distance (x) between these two tribo-
 72 electric layers can be varied under the agitation of mechan-
 73 ical force. After being forced to get in contact with each
 74 other, the contact surface of the two triboelectric layers
 75 will have opposite static charges (tribo-charges), as a result
 76 of contact electrification. Besides the tribo-pairs layer,
 77 there are two electrodes that are carefully insulated inside
 78 the TENG system, which ensures the charges can only
 79 transfer between the two electrodes through external
 80 circuits. If we define the transferred charges from one
 81 electrode to another is Q , one electrode will have the
 82 transferred charge $-Q$ and the other electrode will have
 83 the transferred charge $+Q$.

84 The electrical potential difference between the two
 85 electrodes of any TENGs mainly contributes to two parts.
 86 The first part is from the polarized triboelectric charges and
 87 their contribution to the voltage is $V_{oc}(x)$, which is a
 88 function of separation distance x . Besides, the already
 89 transferred charges Q will also contribute to an electric
 90 potential difference. If we assume no triboelectric charges
 91 exist in this structure, this structure is completely a typical
 92 capacitor, so the contribution of these already transferred
 93 charges between the two electrodes is $-Q/C(x)$, where C is
 94 the capacitance between the two electrodes. Therefore,
 95 due to the electrical potential superposition principle, the
 96 total voltage difference between the two electrodes can be
 97 given by [6]

$$98 \quad V = -\frac{1}{C(x)}Q + V_{oc}(x) \quad (1) \quad 107$$

99 Eq. (1) (named as V - Q - x relationship) is the governing
 100 equation of any TENGs, clearly explaining its inherent capa-
 101 citive behavior [6]. The separation of the polarized tribo-
 102 charges will generate an electrical potential difference
 103 between the two electrodes. If the external circuit exists
 104 between the two electrodes, this electrical potential will
 105 drive electrons to flow from one electrode to another. These
 106 already-transferred electrons can further screen the electrical
 107 potential between the two electrodes [7]. Under short-circuit
 108 conditions, these transferred charges (Q_{sc}) fully screen the
 109 electrical potential generated from polarized triboelectric
 110 charges. Therefore, the following equation can be easily
 111 derived for TENGs under short-circuit conditions [8]:

$$112 \quad 0 = -\frac{1}{C(x)}Q_{sc}(x) + V_{oc}(x) \quad (2) \quad 123$$

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